

**IONIZING RADIATION EFFECT OF GAMMA
RAY AND NEUTRON FLUX ON n-ZnO/p-
CuGaO₂ HETEROJUNCTION DIODE FOR
FLEXIBLE SPACE ELECTRONICS
APPLICATION**

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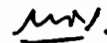
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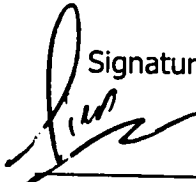
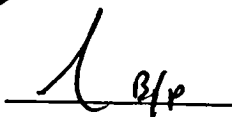
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ABSTRACT

Space electronics based on invisible circuitry requires both transparent n-type and p-type oxide-based semiconductor materials as active channel layers to make circuit design more flexible. However, in space, semiconductor devices are vulnerable to various effect of high energy level of radiation causing single event upsets (SEU), damaging or altering the lattice structure. In this work, n-ZnO/p-CuGaO₂ was selected due to its relatively wide bandgap and a visibility transmittance up to 75%, has wide bandgap of II-VI semiconductor group (~3.3-3.4 eV), a high electron mobility, easily fabricated under low temperature, an efficient photon emission and high conductivity. P-CuGaO₂ and n-ZnO thin films were deposited by using radio frequency (RF) powered sputtering method on indium tin Oxide (ITO) with a base pressure of 9×10^{-3} Torr, at 300 °C deposition temperature, an Argon gas flow of 10 sccm, a radio frequency power of 100 Watt and deposition time of 30 minutes. Once the deposition of the active and confining layer has been fabricated, a silver (Ag) paste was applied as the contacting layer. Structural morphology, optical and electrical properties of both n-ZnO/p-CuGaO₂ thin film and heterojunction diode were investigated before and after irradiation. Fabricated samples were then irradiated at SINAGAMA and NUR II facility. The samples were irradiated using Cobalt-60, gamma-ray with a dose ranging from 10 kGy to 200 kGy and separately a neutron flux of 2×10^{14} n/cm², 9.5×10^{14} n/cm² and 6.5×10^{15} n/cm². The structural properties reveal that p-CuGaO₂ and n-ZnO films, shows the degradation of grain size after irradiation and has a lower diffraction peak with an increase in the Full width half maximum (FWHM). The optical properties of deposited p-CuGaO₂ thin film and n-ZnO, exhibits approximately 75% and 80% respectively in the invisible region at pre-irradiation and post-irradiation due to gamma shows a decrease of optical transmittance up to 55% and 70% at 200 kGy. A decrease in band gap was also tabulated from the transmittance and shows a decrease from 3.85 eV to 3.62 eV for CuGaO₂ and 3.50 eV to 3.28 eV for ZnO after exposure towards gamma irradiation. However, exposure towards neutron flux of 6.5×10^{15} n/cm² only shows small significant changes with transmittance increasing to 85% and 80% for p-CuGaO₂ and n-ZnO, with a band gap of 3.84 eV and 3.50 eV.

As the samples were irradiated with gamma ray, the high energy particle loses its energy in small steps through the interaction with electrons in the materials causing nuclear Collision. This will then in turn create defects in the material such as the formation of color centers (*Farbe center*) that absorbs the signal photons which results to the degradation of the light transmission efficiency of the thin film. On the I-V properties, the decrease in the turn-on voltage of the diode varies with increasing radiation dose for both gamma and neutron flux exposure. The maximum, turn-on-voltage of the prepared diode was shown to be 1.5 V. Exposure towards gamma, shows that the turn-on-voltage has a higher turn-on-voltage of 4.7 V at 200 kGy. However, the effect of neutron flux at 6.5×10^{15} n/cm² shows a small significant difference of 1.7 V. Results shows moderate mitigation towards irradiation, indicating that n-ZnO/p-CuGaO₂ thin film is capable of withstanding harsh radiation environment while still retaining its semiconductor as the changes in band gap ranges between 3 eV to 4 eV after post-irradiation

ABSTRAK

KESAN SINARAN PENGIONAN SINAR GAMMA DAN FLUKS NEUTRON TERHADAP DIOD SIMPANG HETERO n -ZnO/ p -CuGaO₂ UNTUK APLIKASI ELEKTRONIK FLEKSIBEL DI ANGKASA LEPAS

Teknologi elektronik di angkasa lepas berasaskan litar lutsinar memerlukan kedua-dua semikonduktor logam oksida jenis n dan p sebagai lapisan saluran aktif untuk membentuk litar elektronik yang fleksibel. Namun begitu, di angkasa lepas, diod semikonduktor terdedah dengan pelbagai kesan tenaga radiasi bertenaga tinggi yang menyebabkan "single event upsets" (SEU), kemerosotan atau kecacatan kekisi. Dalam kajian ini, n -ZnO/ p -CuGaO₂ telah dipilih kerana sampel ini mempunyai jurang tenaga optik yang luas, kehantaran sifat optik yang tinggi iaitu sebanyak 75%, kumpulan jurang tenaga yang luas dalam semikonduktor II-VI (~ 3.3 - 3.4 eV), mobiliti elektron yang tinggi, suhu fabrikasi yang rendah, pancaran foton yang cekap dan konduksi yang tinggi. Filem nipis p -CuGaO₂ dan n -ZnO telah difabrikasikan menggunakan teknik pemercikan Magnetron Frekuensi Radio di atas substrat indium tin oxide (ITO) dengan tekanan 9×10^{-3} Torr pada suhu 300 °C berserta aliran gas Argon pada kadar 10 sccm, tenaga RF 100 Watt dan pemendapan selama 30 minit. Setelah pemendapan disiapkan, adunan konduktif perak disalut sebagai saluran aktif diod. Struktur morfologi, sifat optik dan sifat elektrik diod simpang-hetero dan filem nipis n -ZnO/ p -CuGaO₂ dikaji sebelum dan selepas didedahkan kepada sinaran. Sampel telah didedahkan kepada sinaran di SINAGAMA dan NUR II untuk proses radiasi. Pendedahan ini melingkungi sinaran Cobalt-60, serakan gamma dengan dos 10 kGy hingga 200 kGy dan serakan neutron dengan fluks sebanyak 2×10^{14} n/cm², 9.5×10^{14} n/cm² and 6.5×10^{15} n/cm². Struktur morfologi yang dikaji menunjukkan bahawa sampel mengalami kemerosotan pada saiz butir selepas pengionan dan serakan oleh sinar gamma dan mempunyai puncak belauan yang rendah dalam lebar lengkap separa maksimum (FWHM). Sifat optik filem nipis p -CuGaO₂ dan n -ZnO masing-masing mempunyai ketelusan sebanyak 75% dan 80% sebelum disininari dan serakan radiasi menunjukkan penurunan dalam kepancaran optik sebanyak 55% dan 70% pada 200 kGy. Data juga menunjukkan penurunan pada jurang tenaga optik dari 3.85 eV ke 3.62 eV bagi CuGaO₂ dan 3.50 eV hingga ke 3.28 eV untuk ZnO selepas serakan

gamma. Walau bagaimanapun, serakan neutron dengan fluks 6.5×10^{15} n/cm² hanya menunjukkan perubahan yang kecil dengan penurunan kepancaran sifat optik sebanyak 72% dan 75% untuk p-CuGaO₂ dan n-ZnO dengan jurang lebar 3.84 eV dan 3.50 eV. Penurunan dalam kepancaran sifat optik adalah disebabkan pembentukan "Farbe center" pada filem nipis yang telah disinari oleh gamma. Untuk sifat keelektrikan, penurunan dalam voltan putaran diod adalah dihubungkan dengan dos radiasi untuk serakan gamma dan neutron. Voltan putaran maksima untuk diod yang disediakan adalah sebanyak 1.5 V. Serakan gamma terhadap diod menunjukkan peningkatan dalam voltan putaran. Tetapi, serakan neutron dengan fluks 6.5×10^{15} n/cm² menunjukkan perubahan kecil sebanyak 1.7 V sahaja. Keputusan menunjukkan mitigasi yang sederhana terhadap serakan radiasi, bahawa n-ZnO/p-CuGaO₂ mampu menangani keadaan radiasi yang tinggi dan mengekalkan sifat semikonduktor dengan rangkaian jurang tenaga optik, 3 eV hingga ke 4 eV selepas serakan radiasi.

TABLE OF CONTENTS

TITLE	i
DECLARATION	ii
CERTIFICATION	iii
ACKNOWLEDGEMENT	iv
<i>ABSTRACT</i>	v
<i>ABSTRAK</i>	vii
TABLE OF CONTENTS	ix
LIST OF TABLES	xiv
LIST OF FIGURES	xvi
LIST OF ABBREVIATIONS	xxi
LIST OF SYMBOLS	xxiii
LIST OF APPENDICES	xxv
CHAPTER 1 : INTRODUCTION	1
1.1 Background Studies	1
1.2 Problem statement	3
1.3 Research Objective	4
1.4 Research Scope	4
1.5 Thesis Outline	4



CHAPTER 2 : LITERATURE REVIEW	7
2.1 Radiation Environment of Semiconductor	7
2.1.1 Natural Environment	7
2.1.2 Nuclear Environment	8
2.1.3 Space Environment	8
2.1.4 High Energy Physics Experiment	12
2.2 Gamma-rays	13
2.2.1 Properties of Gamma-rays	13
2.2.2 Gamma Emission and Internal Conversions	14
2.3 Neutron Fluence	15
2.4 Semiconductors Materials	15
2.4.1 n-Type Semiconductor	16
2.4.2 p-Type Semiconductor	17
2.4.3 n-ZnO Thin film	18
2.4.4 p-CuGaO ₂ Thin film	21
2.5 Thin Film Deposition Method	24
2.5.1 Sputtering	24
2.5.2 Chemical Vapor Deposition	26
2.5.3 Sol-gel Method	27
2.6 Study of Ionizing Radiation Effects on Semiconductor Devices	28
2.6.1 Study of Ionizing Effects on ZnO based Semiconductor	29
2.6.2 Study of Radiation Effects on Cu based Semiconductor	38

2.6.3	Study of Ionizing Radiation Effects on The Ideality factor of ZnO Schottky Diode	40
2.7	Research Direction	43
CHAPTER 3 : METHODOLOGY		44
3.1	Introduction	44
3.2	Substrate Preparation	46
3.2.1	Substrate Cutting	46
3.2.2	Substrate Cleaning	46
3.3	Thin Film and Device Fabrication Steps	48
3.3.1	Fabrication of n-ZnO Thin Films	49
3.3.2	Fabrication of p-CuGaO ₂ Thin Films	51
3.3.3	Fabrication of Transparent Heterojunction Diode	53
3.4	Thin Film Characterization Techniques	55
3.4.1	X-Ray Diffraction	55
3.4.2	Ultraviolet-Visible Spectroscopy	58
3.4.3	Current Voltage Characterization	60
3.5	Scanning Electron Microscope	62
3.6	SRIM-TRIM Simulation	62
3.7	Irradiation Process	65
3.7.1	Gamma-Ray	65
3.7.2	Neutron Fluence	67

CHAPTER 4 : RESULTS AND DICUSSION	69	
4.1	Introuduction	69
4.2	Simulation of ^{60}Co Ions Effects on the Heterojunction Diode	69
4.2.1	Effects of Incident Energy of Cobalt-60 (^{60}Co) Ion	71
4.3	Effects of Gamma Ray Irradiation on Semiconductor Device	76
4.3.1	Structural Properties of Gamma Irradiatited n-ZnO and p-CuGaO ₂ thin film	
4.3.2	Surface Profile of Gamma-Irradiated n-ZnO	80
4.3.3	Optical Properties of Gamma-irradiated n-ZnO	81
4.3.4	Effects of Gamma Ray on Structural properties of p-CuGaO ₂	84
4.3.5	Surface Profile of Gamma-Irradiated p-CuGaO ₂	87
4.3.6	Optical Properties of Gamma-irradiated p-CuGaO ₂	88
4.4	Neutron Fluence Effects on Radiation on Semiconductor Device	91
4.4.1	Strucutral Properties of Neutron Fluence on n-ZnO Thin Film	93
4.4.2	Surface Profile of Neutron Fluence on n-ZnO	95
4.4.3	Optical Properties of Neutron Fluence on n-ZnO	96
4.5	Effects of Neutron Fluence on p-CuGaO ₂ Thin Film	98
4.5.1	Structural Properties of Neutron Fluence on p-CuGaO ₂	98
4.5.2	Surface Profile of Neutron Fluence on p-CuGaO ₂	100
4.5.3	Optical Properties of Neutron Fluence on p-CuGaO ₂	101

4.6	Effects of Neutron Fluence on p-CuGaO ₂ Thin Film	103
4.6.1	Gamma-Ray Effect	103
4.6.2	Neutron Fluence Effect	111
CHAPTER 5 : CONCLUSION		115
5.1	Introduction	115
5.2	Effects of Gamma-Rays and Neutron Flux on the Thin Films and Device	116
5.3	Effects of Gamma-Rays and Neutron Flux on the Electrical Parameters	117
5.4	Difference between γ Rays and Neutron Fluence	118
5.5	Simulation Results utilizing ⁶⁰ Co	118
5.6	Future work	119
REFERENCES		121
APPENDICES		135

LIST OF TABLES

	Page
Table 2.1: Fundamental Properties of ZnO	19
Table 2.2: p-Type Tos with respective characteristic	23
Table 2.3: Summary of Current research work related to ZnO	37
Table 2.4: Review of Electrical properties of ZnO based Schottky Diodes	23
Table 3.1: Deposition Parameter of ZnO thin films	50
Table 3.2: Deposition Parameter of CuGaO ₂ thin films	53
Table 3.3: Transparent heterojunction diode deposition parameter	54
Table 3.4: Parameter of simulation	64
Table 3.5: Experimental Setup details at MINTec-Sinagama	66
Table 3.6: Experimental details at NUR II facility	68
Table 4.1: The FWHM, Grain Size and Lattice constant of the Unirradiated and gamma Irradiated p-CuGaO ₂	80
Table 4.2: The Optical Transmittance and Band Gap of Un-irradiated and Irradiated CuGaO ₂ at 10 kGy, 50 kGy, 100 kGy, 150 kGy, 200 kGy	86
Table 4.3: The Optical Transmittance and Band Gap of Un-irradiated and Irradiated CuGaO ₂ at 10 kGy, 50 kGy, 100 kGy, 150 kGy, 200 kGy	91
Table 4.4: The FWHM, Grain size and Lattice constant of the Neutron Irradiated and Un-irradiated and neutron irradiated n-ZnO thin films.	95

Table 4.5:	The FWHM, Grain size and Lattice constant of the Neutron Irradiated and Un-irradiated p-CuGaO ₂ thin films.	100
Table 4.6:	Electrical parameters of the Un-irradiated, 10 kGy, 50 kGy, 100 kGy, 150 kGy, 200 kGy, n-ZnO/p-CuGaO ₂ heterojunction	104
Table 4.7:	Electrical parameters of the n-ZnO/p-CuGaO ₂ heterojunction diode at different Neutron Fluence	112

LIST OF FIGURES

	Page
Figure 2.1: The explorer I	9
Figure 2.2: Semiconductor doped with pentavalent atoms	17
Figure 2.3: Semiconductor doped with trivalent atoms.	18
Figure 2.4: Hexagonal wurtzite crystal structure of ZnO	19
Figure 2.5: Different p-type TOS lattice constant matching with ZnO lattice constant.	21
Figure 2.6: Cubic cuprite crystal structure of CuGaO ₂	22
Figure 2.7: Sputtering system	25
Figure 2.8: Chemical Vapor Deposition (CVD)	27
Figure 2.9: Pair Production- Energy conversion to mass	29
Figure 2.10: Comparison of turn-on voltage shift as a function of irradiation dose for different material systems. ZnO TFTs show relatively small changes with large radiation dose and has greater superiority than conventional covalent silicon material.	31
Figure 2.11: The XRD spectra result of the pristine and irradiated ZnO thin films irradiated with 5 MeV protons with different irradiation doses	33
Figure 2.12: Transfer characteristic in the IZO TFT before and after irradiation	35
Figure 3.1: Flowchart of the research Methodology	45
Figure 3.2: Glass Cutter	46

Figure 3.3:	Chemicals used for substrate cleaning (Methanol, Acetone , Distilled water)	47
Figure 3.4:	Substrate cleaned using the Ultrasonic bath	47
Figure 3.5:	Substrate is dried using nitrogen gas.	48
Figure 3.6:	The Structural design of n-ZnO/p-CuGaO ₂ diode with a substrate base of Indium tin Oxide (ITO) glass	48
Figure 3.7:	The inside sketch of magnetron sputtering.	49
Figure 3.8:	ZnO ceramic Target	49
Figure 3.9:	Structural Design of the n-ZnO Thin Film	51
Figure 3.10:	CuGaO ₂ ceramic target	52
Figure 3.11:	Structural Design of the p-CuGaO ₂ thin film	53
Figure 3.12:	The Structural design of n-ZnO/p-CuGaO ₂ diode with a substrate base of Indium tin Oxide (ITO) glass.	55
Figure 3.13:	X-ray diffraction of atom in crystal plane.	56
Figure 3.14:	Full width half maximum obtained from an XRD result	57
Figure 3.15:	A light beam entering a material	58
Figure 3.16:	I-V Keithley MSU 2400	60
Figure 3.17:	The Tote Irradiator used in MINTec-Sinagama	66
Figure 3.18:	The cut away view of the MINT TRIGA MARK II Reactor	67
Figure 3.19:	The side view of the MINT TRIGA MARK II Reactor	68
Figure 4.1:	Stopping range of Cobalt-60 in ZnO/CuGaO ₂ based heterojunction device	71

Figure 4.2:	Target displacement and Energy absorbed of ZnO:CuGaO ₂ heterojunction device at different incident energy level	72
Figure 4.3:	Plot depth versus Y-axis at at (a) $E_{co}= 500$ keV ,(b) $E_{co}= 5000$ keV , (c) 10000 keV in ZnO: CuGaO ₂ heterojunction device.	75
Figure 4.4:	Ionization of ⁶⁰ Co against the energy level	76
Figure 4.5:	X-ray diffraction (XRD) spectra of ZnO at pre-irradiation and ionizing dose of 10,50,100,150 and 200 kGy respectively.	78
Figure 4.6:	The relation of FWHM and Grain Size with increasing total ionizing dose (TID) for ZnO thin film	79
Figure 4.7:	The SEM images of the surface morphology of a) Un-irradiated ZnO , Irradiated at, b) 10 kGy, c) 50 kGy, d) 100 kGy e) 150 kGy, 200 kGy	81
Figure 4.8:	The translucency of ZnO as grown, a) un-irradiated, b) 10kGy, c) 50kGy, d) 100kGy, e) 150kGy, f) 200kGy	82
Figure 4.9:	The transmittance of ZnO as grown, Irradiated at,10kGy, 50kGy, 100kGy, 150kGy, 200kGy	83
Figure 4.10:	The $(\alpha h\nu)^2$ vs $h\nu$ (eV) plot of ZnO	84
Figure 4.11:	X-ray diffraction (XRD) spectra of CuGaO ₂ at pre-irradiation and ionizing dose of 10 kGy, 50kGy, 100 kGy,150 kGy and 200 kGy, respectively	85
Figure 4.12:	The relation of FWHM and Grain Size with increasing TID for p-CuGaO ₂ thin film	87
Figure 4.13:	The SEM images of the surface morphology of a) ZnO as grown, Irradiated at, b) 10 kGy, c) 50 kGy, d) 100 kGy e) 150 kGy, f) 200 kGy	88

Figure 4.14:	The translucency of p-CuGaO ₂ , a) un-irradiated, b) 10 kGy, c) 50 kGy, d) 100 kGy, e) 150 kGy, f) 200 kGy	89
Figure 4.15:	Optical Transmittance of CuGaO ₂ a) Un-irradiated and Irradiated CuGaO ₂ b)10kGy, c) 50kGy, d)100kGy, e) 150kGy, f) 200kGy	90
Figure 4.16:	The $(\alpha h\nu)^2$ vs photon energy (eV) plot of CuGaO ₂	91
Figure 4.17:	Various defects created due to atomic displacement in lattice structure	93
Figure 4.18:	X-ray diffraction (XRD) spectra of Un-irradiated and Irradiated with neutron flux of a) 2×10^{14} n/cm ² , b) 9.5×10^{14} n/cm ² c) 6.5×10^{15} n/cm ² of ZnO	97
Figure 4.19:	The SEM images of the surface morphology of ZnO at a)Un-irradiated, 2×10^{14} n/cm ² , b) 9.5×10^{14} n/cm ² c) 6.5×10^{15} n/cm ²	96
Figure 4.20:	The transmittance of un-irradiated ZnO and Irradiated with neutron flux of 2×10^{14} n/cm ² , 9.5×10^{14} n/cm ² and 6.5×10^{15} n/cm	97
Figure 4.21:	The transmittance of un-irradiated ZnO as grown. Irradiated at 2×10^{14} n/cm ² , 9.5×10^{14} n/cm ² , 6.5×10^{15} n/cm.	98
Figure 4.22:	X-ray diffraction (XRD) spectra of p-CuGaO ₂ at pre-irradiation and a flux of a) 2.0×10^{14} n/cm ² , b) 9.5×10^{14} n/cm ² c) 6.5×10^{15} n/cm ²	99
Figure 4.23:	The SEM images of the surface morphology of a) un-irradiated ZnO and irradiated with neutron flux of b) 2×10^{14} n/cm ² , c) 9.5×10^{14} n/cm ² d) 6.5×10^{15} n/cm ²	101
Figure 4.24:	The transmittance of p-CuGaO ₂ of un-irradiated and Irradiated at, 2×10^{14} n/cm ² , 9.5×10^{14} n/cm ² , 6.5×10^{15} n/cm	102

Figure 4.25:	The band gap of p-CuGaO ₂ of un-irradiated and Irradiated at 2×10^{14} n/cm ² , 9.5×10^{14} n/cm ² , 6.5×10^{15} n/cm	102
Figure 4.26:	Structure of transparent heterojunction n-ZnO/p-CuGaO ₂ diode	103
Figure 4.27:	I-V characteristic of n-ZnO/p-CuGaO ₂ heterojunction diode at different total ionizing dose.	105
Figure 4.28:	The $dV/d \ln J$ vs J plot of n-ZnO/p-CuGaO ₂ heterojunction	110
Figure 4.29:	I-V characteristic of n-ZnO/p-CuGaO ₂ heterojunction diode at different neutron flux	111
Figure 4.30:	The $dV/d \ln J$ vs J plot of n-ZnO/p-CuGaO ₂ heterojunction due to neutron	114

LIST OF ABBREVIATIONS

AC	-	alternating current
ALICE	-	A large Hadron Collider Experiment
ATLAS	-	A Toroidal LHC Apparatus
BJT	-	Bipolar Junction Transistor
CERN	-	European Organization for Nuclear Research
CME	-	Coronal Mass Ejections
CMS	-	Compact Muon Solenoid
CuGaO ₂	-	Copper Gallium Oxide
DC	-	Direct Current
Fet	-	Field Effect Transistor
FWHM	-	Full Width Half Maximum
GCR	-	Galactic Cosmic Rays
GeV	-	Gigaelectron Volt
HOMO	-	Highest occupied molecular orbital
IMF	-	Intraplanetary Magnetic Field
I-V	-	Current -Voltage
IZO	-	Indium Zinc Oxide
KeV	-	Kiloelectron Volt
Km/hr	-	Kilometer per Hour
LHC	-	Large Hadron Collider
MIS	-	metal-insulator -semiconductor



MOCVD	-	Metal organic chemical vapor deposition
NASA	-	National Aeronautics and Space Administrations
PLD	-	Pulse Laser Deposition
Rad	-	Radiation Absorbed Dose
SAA	-	South Atlantic Anomaly
SEE	-	Single Event Effects
SEU	-	Single event Upsets
Si	-	Silicon
Si:H	-	Hydrogenated Silicon
SPE	-	Solar particle events
SRIM	-	Stopping range of ion matter
TFT	-	Thin film transistor
TNT	-	Trinitrotoluene
TOTEM	-	Total Cross Section, Elastic Scattering and diffraction Dissociation
TRIM	-	Transport range of ion matter
UV-Vis	-	Ultraviolet Visible spectroscopy
XRD	-	X-Ray Diffraction

LIST OF SYMBOLS

%	-	Percent
°	-	Degree
°C	-	Celsius
A	-	Ampere
Å	-	Angstrom
C	-	Capacitance
<i>d</i>	-	Average Grain Size
<i>e</i>	-	Electron with electronic charge of 1.6×10^{-19} C
E_d	-	Average surface binding Energy
E_b	-	Average surface binding Energy before collision
E_f	-	Final Energy
<i>FF</i>	-	Fill Factor
E_i	-	Initial Energy
eV	-	electron volt
Fm	-	Femtometre
γ	-	Gamma
I_o	-	Initial Beam
I	-	Intensity of Emitted Radiation
J_{sc}	-	Current density
K	-	Kelvin
M	-	Mega

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